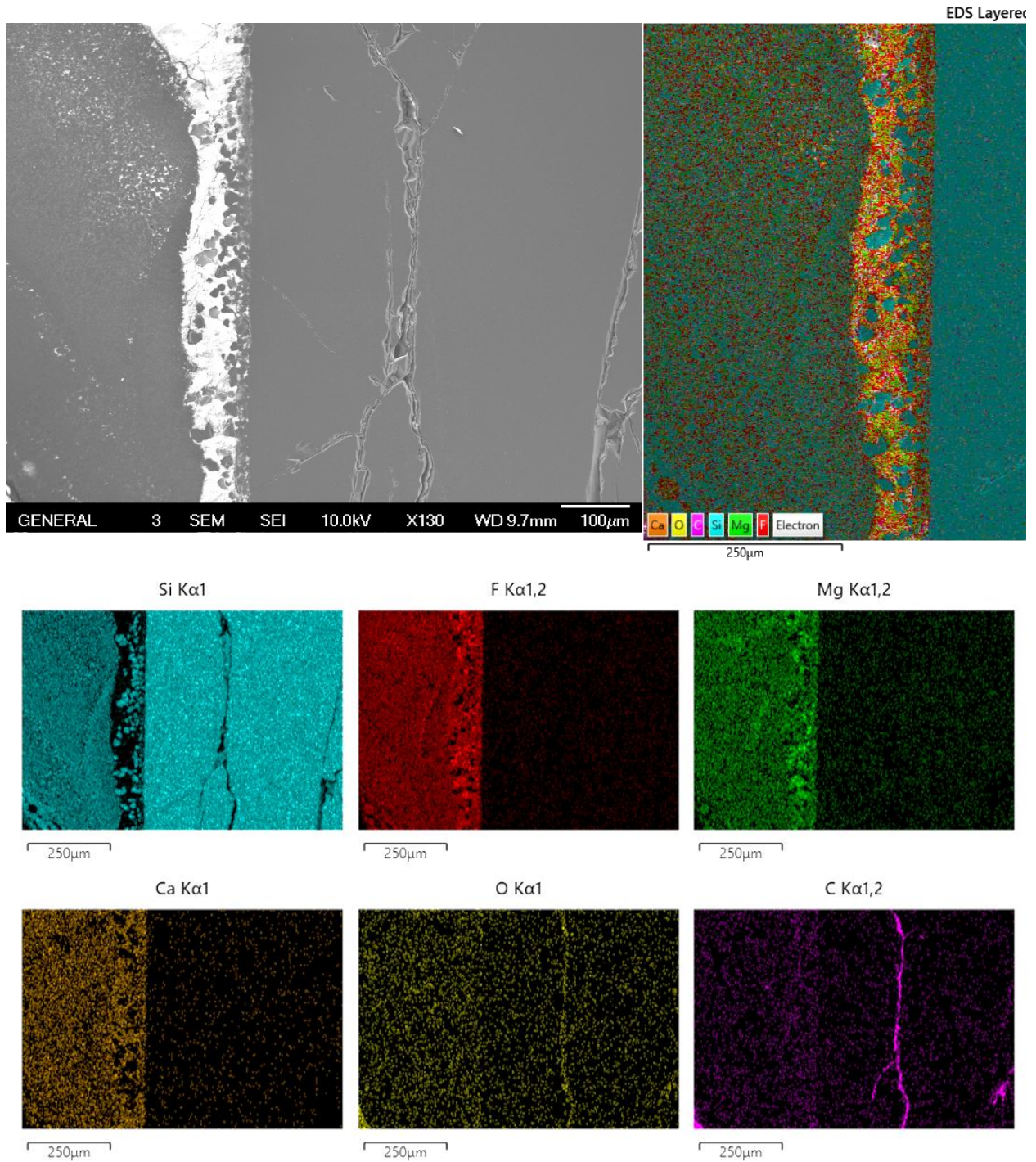The silicon deposit should be characterized applying precise characterization methods, like SEM, EDS, and ICP-MS, to evaluate the purity level of the product. We will need assistance in finding these resources for perform the analyses. Some of the pictures we took for our previous samples are shown below.

For the bulk deposits, the most cost-effective way to predict PV efficiency is by measuring carrier lifetime of silicon. For this reason, after reducing impurities below what can be measured by ICP-MS, we will need resources to measure the carrier lifetime of our solar silicon product. Carrier lifetime is an indicator of the efficiency of a solar cell, and thus is a key consideration in choosing materials for solar cells. The carrier "lifetime" (T) measures how long a carrier is likely to stay around before recombining. Diagram below shows a sample of measuring this parameter. In this diagram (by A. Zarroug et al.), carrier lifetime measurement from top surface of solar cells with different configurations is shown.